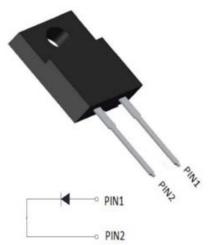


YJD106506FQG2Q

Silicon Carbide Schottky Diode

V _{RRM}	650 V
I _F (127°C)	6 A
Q _C	25 nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: ITO-220AC Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c=25[°]C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106506FQG2
Reverse voltage (repetitive peak) @ Tj=25°C	V _{RRM}	V	650
Reverse voltage (Surge Peak) @ T _j =25°C	V _{RSM}	V	650
Reverse voltage (DC) @ Tj=25°C	V _{DC}	V	650
Continuous forward current @ T _c =25°C		А	12
Continuous forward current @ T _c =127°C	I _F		6
Non-repetitive peak forward surge current @ $T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	А	65
Power Dissipation@ T _c =25°C		31	
Power Dissipation@ T _c =110°C	P _{TOT}	W	13
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	21
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175

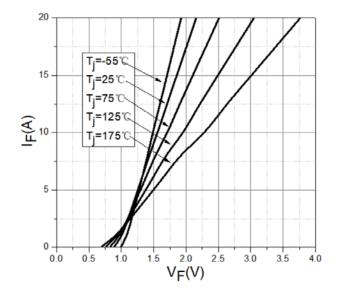
Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.				
E	N	V _F V	I _F =6A, T _j =25°C	1.31	1.5				
Forward voltage drop	VF		I _F =6A, T _j =175°C	1.65	-				
Poverse leakage ourrent	Ι _R μ		V _R =650V, T _j =25°C	0.5	25				
Reverse leakage current		μA	V _R =650V, T _j =175°C	5	-				
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , QC= \int_0^{VR} C(V)dV	25	-				
						V _R =0V, f=1MHZ	378	-	
Total capacitance	С	pF	V _R =200V, f=1MHZ	51	-				
							V _R =400V, f=1MHZ	49	-
Capacitance Stored Energy	Ec	μJ	V _R =400V	3	-				

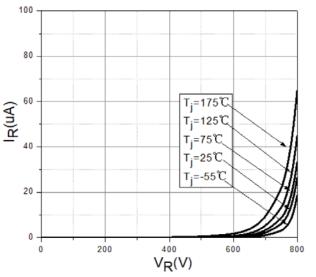
■Thermal Characteristics (Ta=25°C Unless otherwise specified)

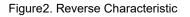
PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{8J-C}	°C W	4.76

■Typical Characteristics









2/5

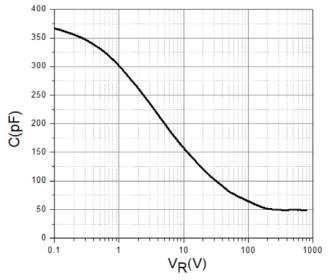
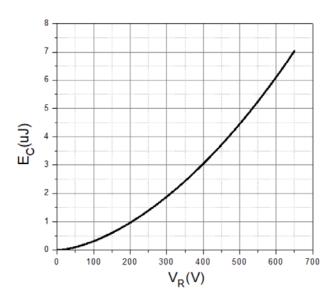
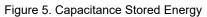
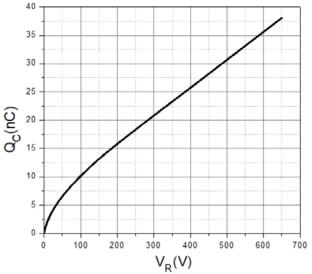
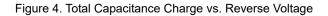


Figure 3. Capacitance vs. Reverse Voltage









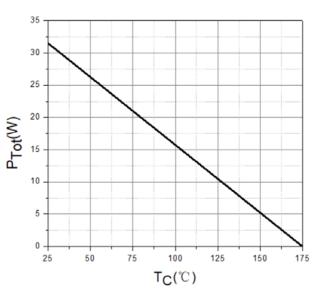
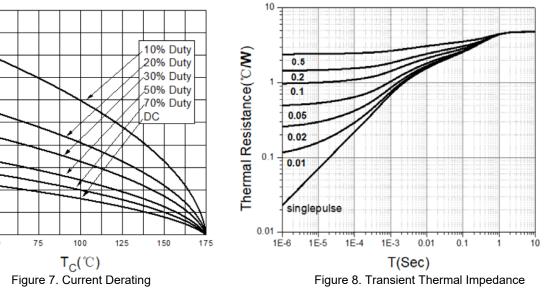


Figure 6. Power Derating



0 25 50

3/5

50

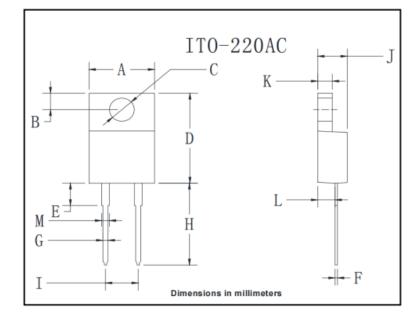
40

10

l_{F(peak)}(A)



Outline Dimensions



ITO-220AC				
Dim	Min	Max		
А	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
E	3.5	4.1		
F	0.45	0.75		
G	0.45	0.75		
Н	13.35	14.15		
I	4.97	5.23		
J	4.3	4.8		
к	2.5	2.74		
L	2.58	2.82		
М	1.03	1.43		



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